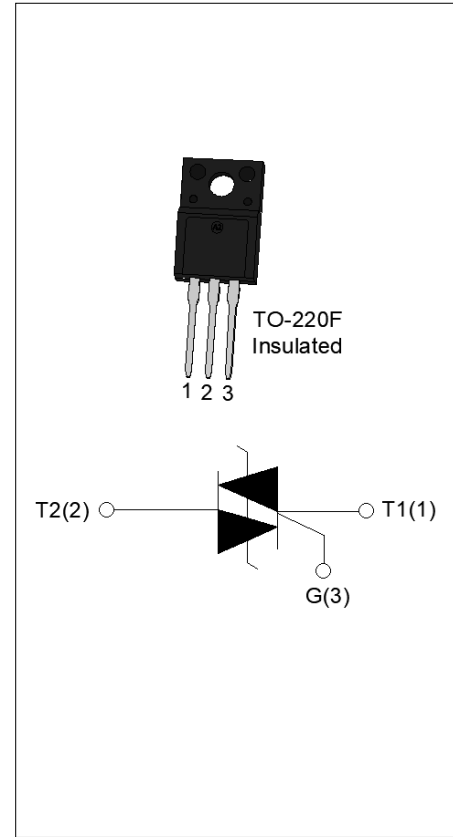


The ACJT625-8F triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. The ACJT625-8F embeds a TVS structure to absorb the inductive turn-off energy such as those described in the IEC 61000-4-5 standards. By using an external plastic package, ACJT625-8F provides a rated insulation voltage of 2000 VRMS, Package TO-220F is RoHS compliant.



Symbol	Value	Unit
$I_{T(RMS)}$	6	A
V_{DRM}/V_{RRM}	800	V
$I_{GT} / /$	25/25/25	mA

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	
Operating junction temperature range	T_j	-40-125	
Repetitive peak off-state voltage ($T_j=25^\circ\text{C}$)	V_{DRM}	800	V
Repetitive peak reverse voltage ($T_j=25^\circ\text{C}$)	V_{RRM}	800	V
RMS on-state current ($T_c = 98^\circ\text{C}$)	$I_{T(RMS)}$	6	A
Non repetitive surge peak on-state current (full cycle, $t_p=20\text{ms}$, $T_j=25^\circ\text{C}$)	I_{TSM}	60	A
Non repetitive surge peak on-state current (full cycle, $t_p=16.6\text{ms}$, $T_j=25^\circ\text{C}$)		66	
I^2t value for fusing ($t_p=10\text{ms}$, $T_j=25^\circ\text{C}$)	I^2t	18	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$, $f=100\text{Hz}$, $T_j=125^\circ\text{C}$)	di/dt	100	A/s
Peak gate current ($t_p=20\text{ }\mu\text{s}$, $T_j=125^\circ\text{C}$)	I_{GM}	4	A

Average gate power dissipation ($T_j=125$)	$P_{G(AV)}$	0.5	W
Peak gate power	P_{GM}	10	W
Peak pulse voltage ($T_j=25$; non-repetitive,off-state;FIG.7)	V_{pp}	3.5	kV

($T_j=25$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12V R_L=33$	- -	MAX.	25	mA
V_{GT}		- -	MAX.	1	V
V_{GD}	$V_D=V_{DRM} T_j=125$ $R_L=3.3K$	- -	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	-	MAX.	40	mA
				60	
I_H	$I_T=100mA$		MAX.	40	mA
dV/dt	$V_D=540V$ Gate Open $T_j=125$		MIN.	2500	V s
(dI/dt) _c	(dV $T_j=125$)		MIN.	8	A/ms
t_{on}	$I_G=40mA I_A=200mA I_R=20mA$ $T_j=25$		TYP.	3	s
t_{off}				30	
V_{CL}	$I_{CL}=0.1mA t_p=1ms$		MIN.	850	V

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=8.5A t_p=380$ s	$T_j=25$	1.5	V
V_{TO}	Threshold voltage	$T_j=125$	0.82	V
R_D	Dynamic resistance	$T_j=125$	64	
I_{DRM}	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25$	5	A
I_{RRM}		$T_j=125$	0.3	mA

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	3.2	/W
$R_{th(j-a)}$	junction to ambient (AC)	60	/W

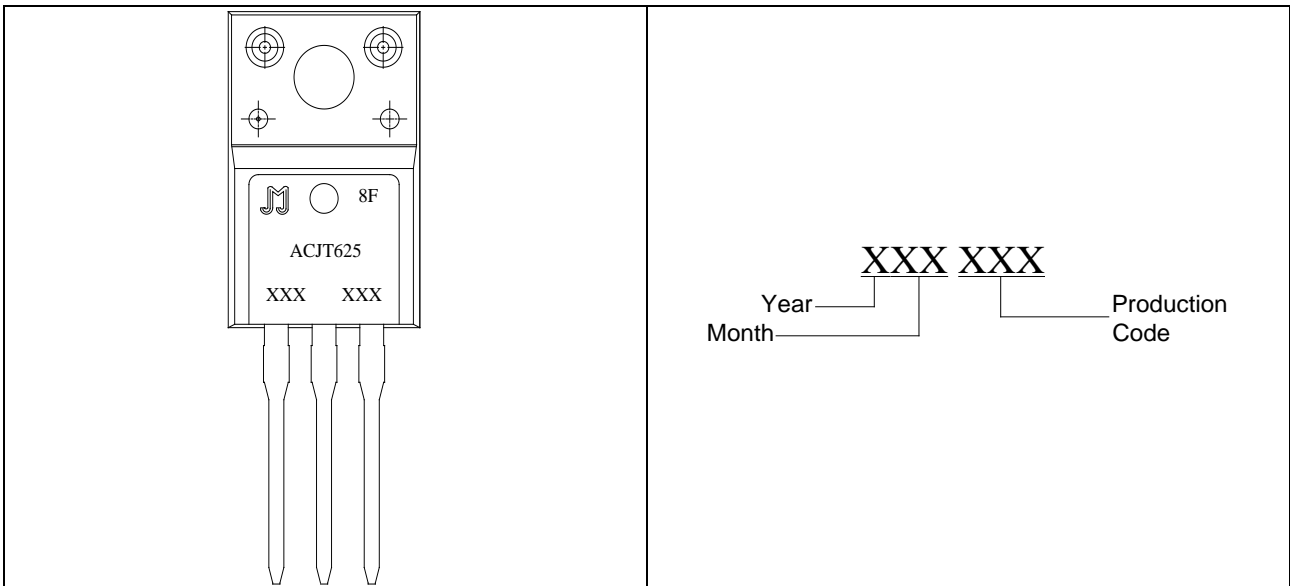
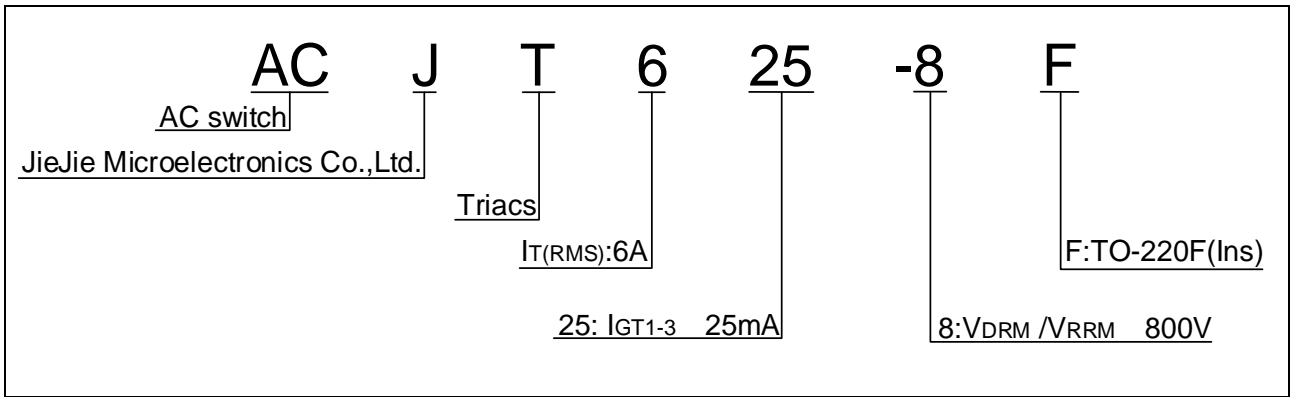


FIG.1 Maximum power dissipation versus RMS on-state current

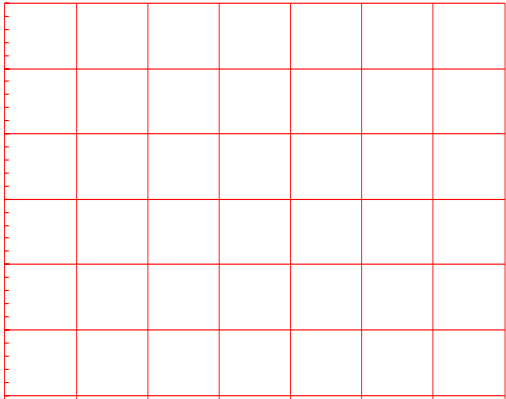
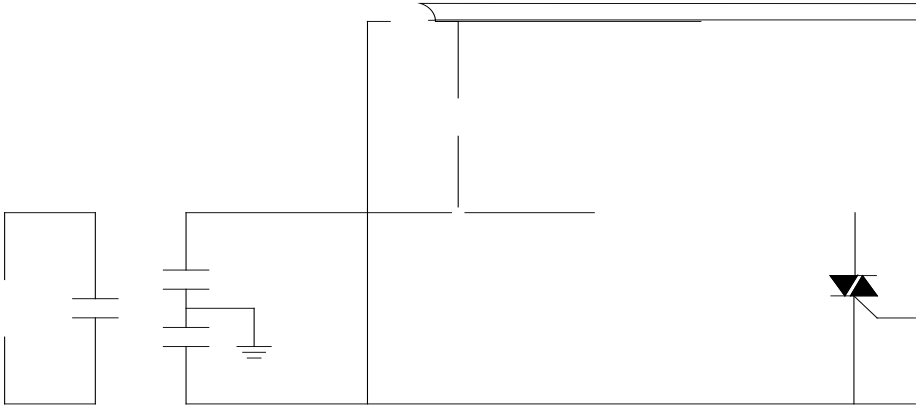
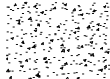


FIG.2: RMS on-state current versus case temperature


FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards





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